



STP80NF03L

N-CHANNEL 30V - 0.004 Ω - 80A TO-220

STripFET™ II MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP80NF03L	30 V	< 0.0045 Ω	80 A

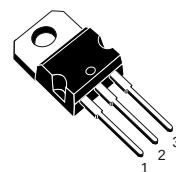
- TYPICAL R_{DS(on)} = 0.004 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW THRESHOLD DRIVE

DESCRIPTION

This Power MOSFET is the latest development of ST-Microelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

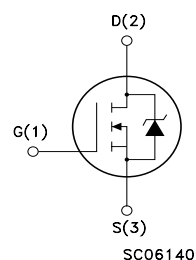
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT
(INJECTION, ABS, AIR-BAG, LAMP DRIVERS
Etc.)



TO-220

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP80NF03L	P80NF03L	TO-220	TUBE

STP80NF03L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage ($V_{GS} = 0$)	30	V
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	30	V
V_{GS}	Gate-source Voltage	± 20	V
I_D (#)	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	80	A
I_D (#)	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	80	A
I_{DM} (●)	Drain Current (pulsed)	320	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating Factor	2.0	W/ $^\circ\text{C}$
dv/dt (1)	Peak Diode Recovery Voltage Slope	2.0	V/ns
T_{stg}	Storage Temperature	-65 to 175	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$

(#) Current Limited by Package.

(●) Pulse width limited by safe operating area.

(1) $I_{SD} \leq 80\text{A}$, $di/dt \leq 240\text{ A}/\mu\text{s}$, $V_{DD} = 24\text{V}$; $T_j \leq T_{JMAX}$.

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.5	$^\circ\text{C}/\text{W}$
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum Lead Temperature For Soldering Purpose Typ	300	$^\circ\text{C}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	40	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 20\text{ V}$)	2.3	J

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED)

OFF/ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125^\circ\text{C}$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1	1.5	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 40\text{ A}$		0.004 0.0045	0.0045 0.0065	Ω Ω

ELECTRICAL CHARACTERISTICS (CONTINUED)**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} = 15\text{ V}$, $I_D = 15\text{ A}$		50		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		5500		pF
C_{oss}	Output Capacitance			1670		pF
C_{rss}	Reverse Transfer Capacitance			290		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		30		ns
t_r	Rise Time			270		ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 24\text{ V}$, $I_D = 80\text{ A}$, $V_{GS} = 4.5\text{ V}$		85 23 40	110	nC nC nC

SWITCHING OFF

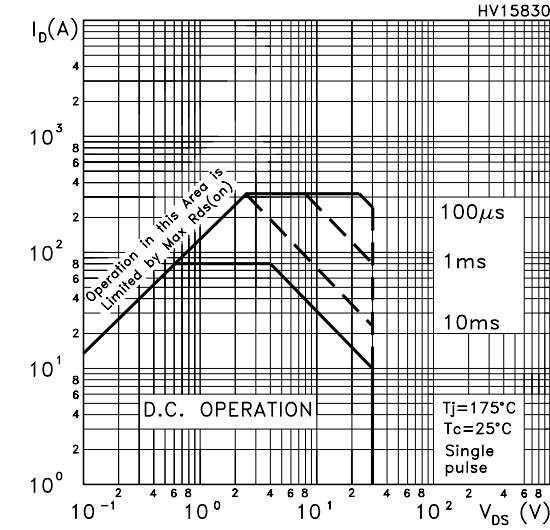
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		110		ns
t_f	Fall Time			95		ns
$t_{r(Voff)}$ t_f t_c	Off-Voltage Rise Time Fall Time Cross-over Time	$V_{clamp} = 24\text{ V}$, $I_D = 80\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$ (Inductive Load, Figure 5)		125 75 125		ns ns ns

SOURCE DRAIN DIODE

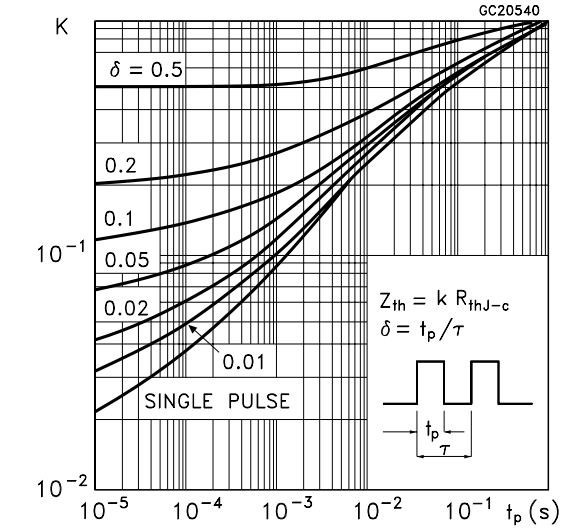
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				80	A
I_{SDM} (1)	Source-drain Current (pulsed)				320	A
V_{SD} (2)	Forward On Voltage	$I_{SD} = 80\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		75 0.15 4		ns μC A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

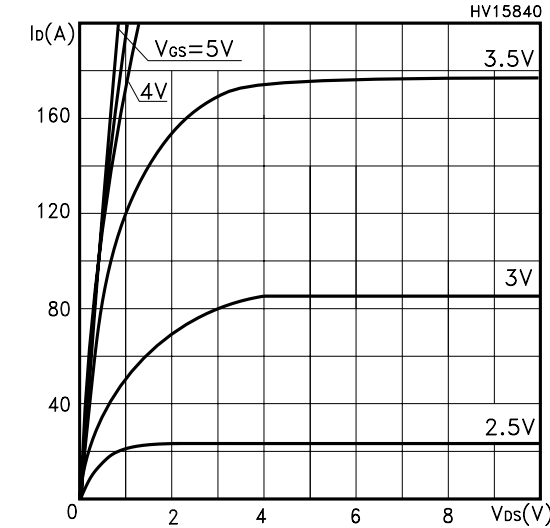
Safe Operating Area



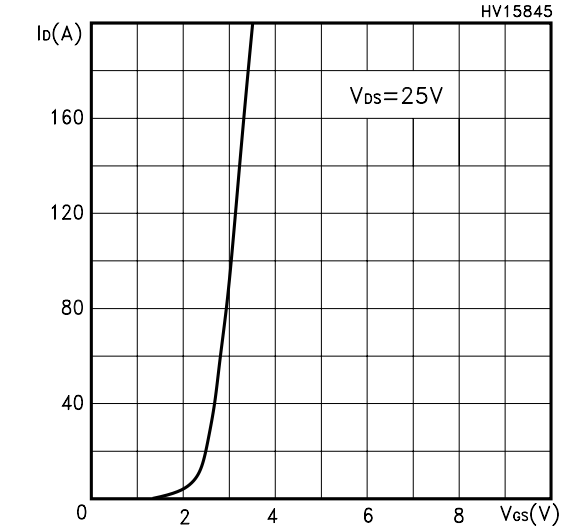
Thermal Impedance



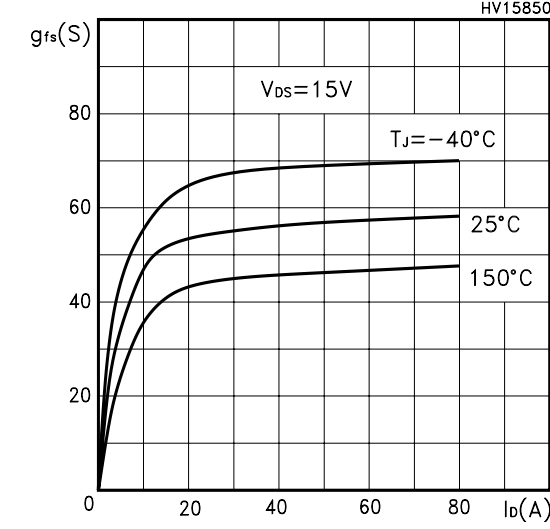
Output Characteristics



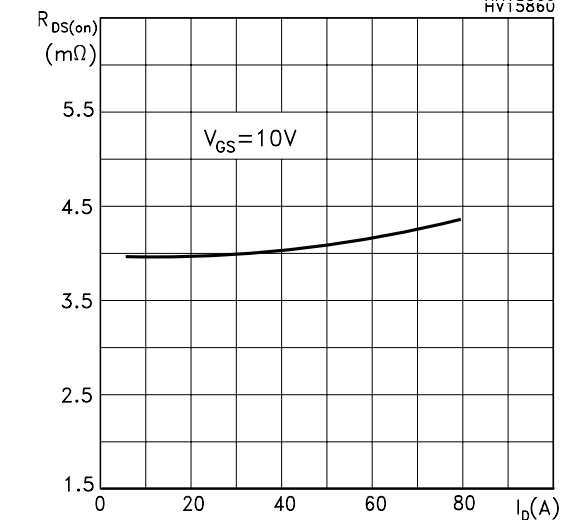
Transfer Characteristics



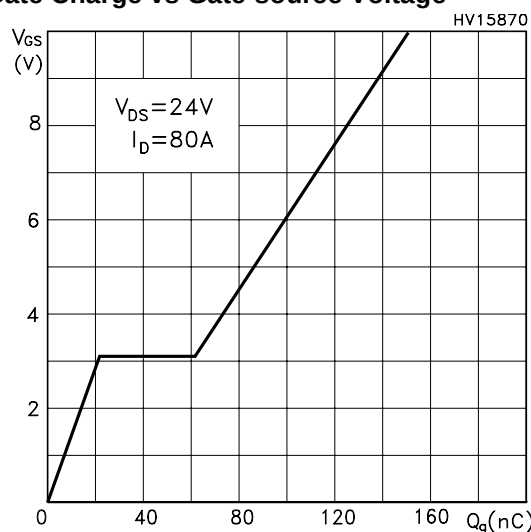
Transconductance



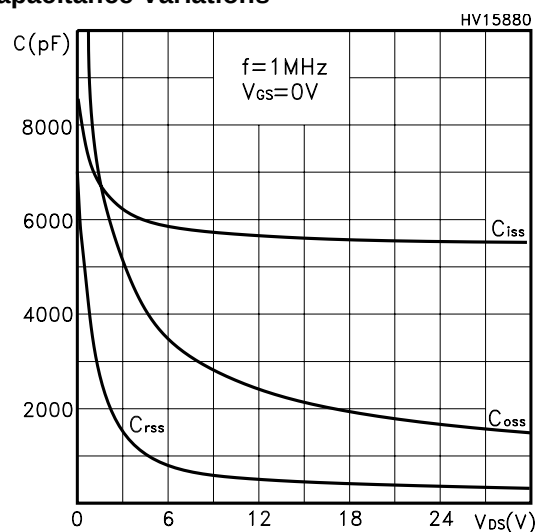
Static Drain-source On Resistance



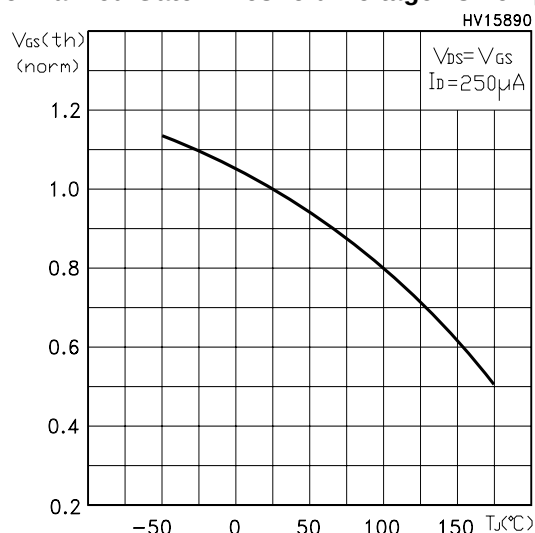
Gate Charge vs Gate-source Voltage



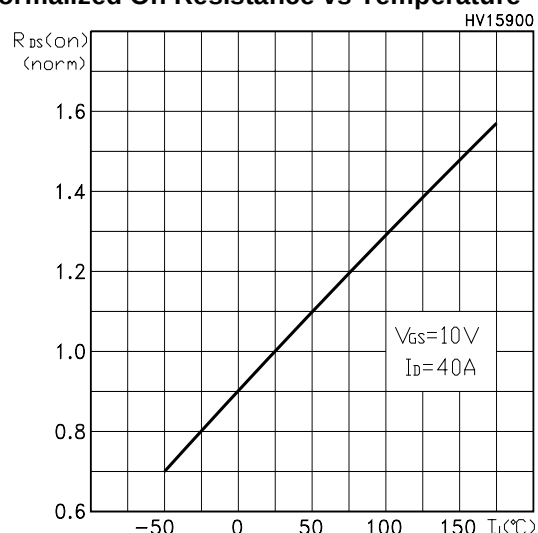
Capacitance Variations



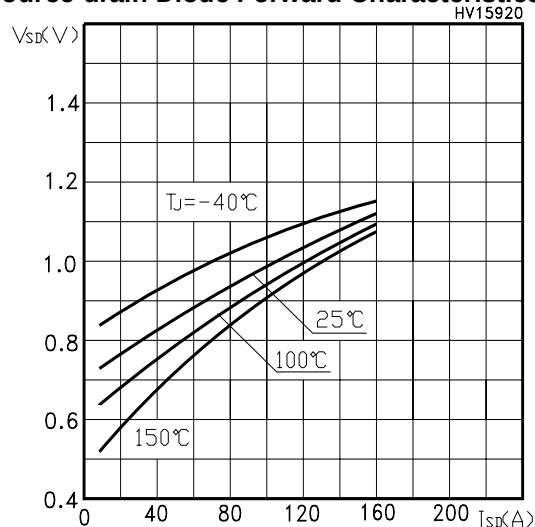
Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature

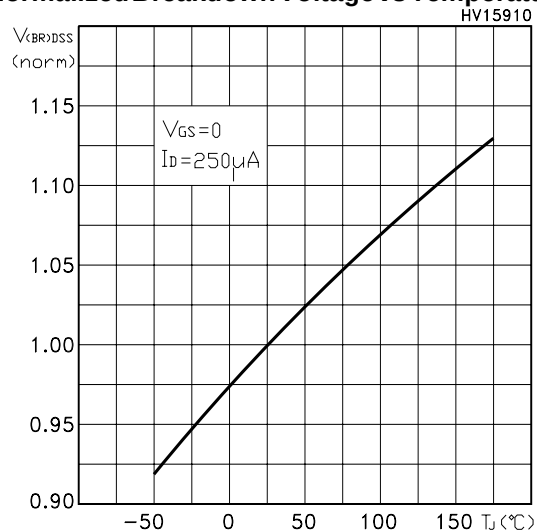


Fig. 1: Unclamped Inductive Load Test Circuit

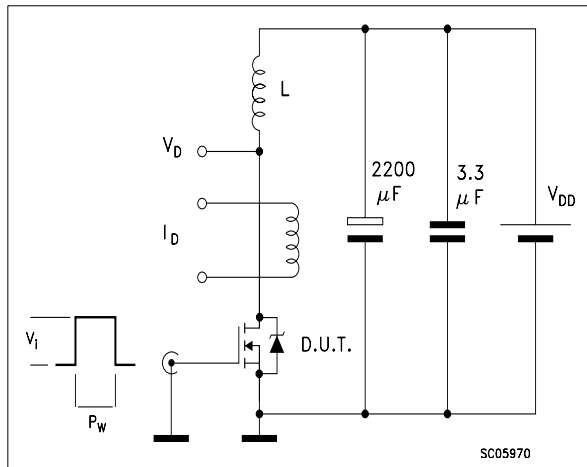


Fig. 2: Unclamped Inductive Waveform

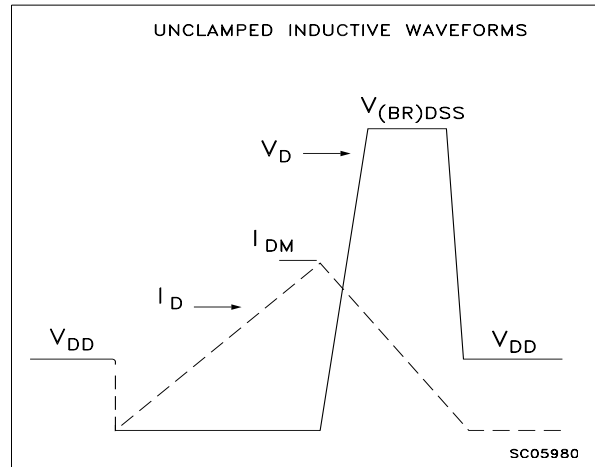


Fig. 3: Switching Times Test Circuit For Resistive Load

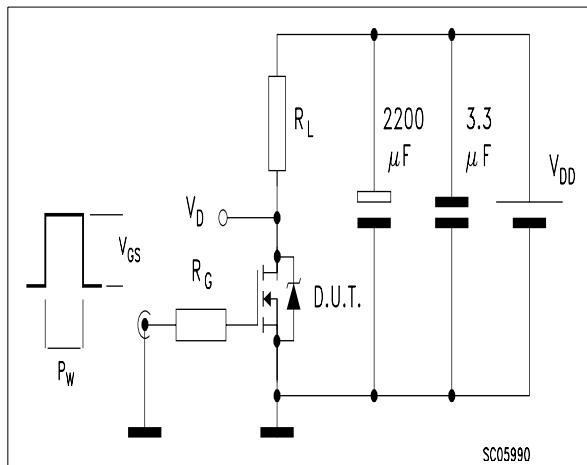


Fig. 4: Gate Charge test Circuit

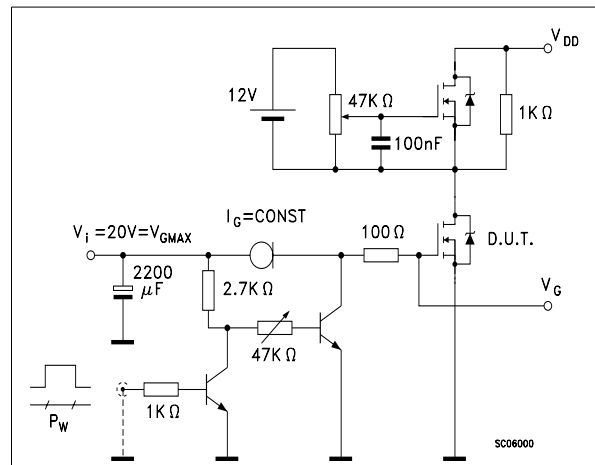
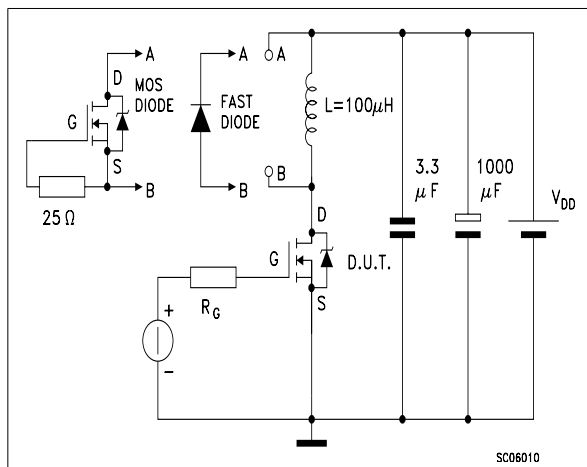
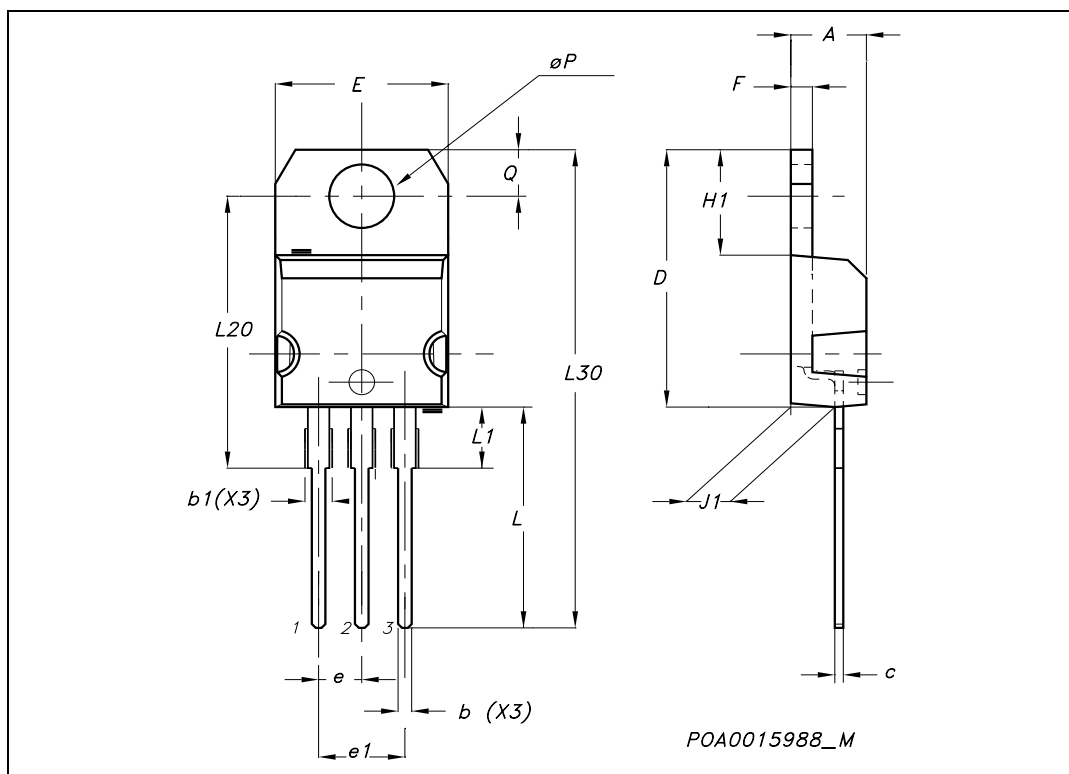


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



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